

## N-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- ☑ Surface-mounted package
- ☑ Low Thermal Resistance

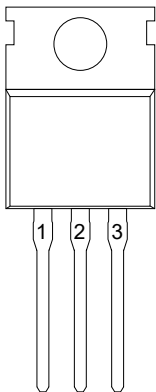
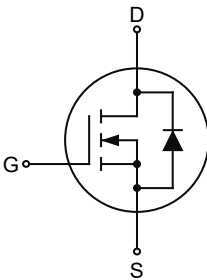
#### 1.2 Applications

- ☑ Motor driver appliances
- ☑ High power inverter system
- ☑ Adapter appliances

#### 1.3 Quick reference

- ☑  $BV \geq 100\text{ V}$
- ☑  $R_{DS(ON)} \leq 9.5\text{ m}\Omega @V_{GS} = 10\text{ V}$
- ☑  $P_D \leq 67\text{ W}$
- ☑  $R_{DS(ON)} \leq 13.5\text{ m}\Omega @V_{GS} = 4.5\text{ V}$
- ☑  $I_D \leq 64\text{ A}$

### 2. Pin Description

| Pin | Description | Simplified Outline                                                                                             | Symbol                                                                                |
|-----|-------------|----------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| 1   | Gate (G)    |  <p>Top View<br/>TO-220</p> |  |
| 2   | Drain (D)   |                                                                                                                |                                                                                       |
| 3   | Source (S)  |                                                                                                                |                                                                                       |

## 3. Limiting Values

| Symbol               | Parameter                                        | Conditions                                    | Min | Max      | Unit                 |
|----------------------|--------------------------------------------------|-----------------------------------------------|-----|----------|----------------------|
| $V_{DS}$             | Drain-Source Voltage                             | $T_C=25^{\circ}\text{C}$                      | 100 | -        | V                    |
| $V_{GS}$             | Gate-Source Voltage                              | $T_C=25^{\circ}\text{C}$                      | -   | $\pm 20$ | V                    |
| $I_D^{*,***}$        | Drain Current (DC)                               | $T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$  | -   | 64       | A                    |
|                      |                                                  | $T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$ | -   | 40       | A                    |
| $I_{DM}^{*}$         | Pulsed Source Current                            | $T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$  | -   | 256      | A                    |
| $P_D$                | Power Dissipation                                | $T_C=25^{\circ}\text{C}$                      | -   | 67       | W                    |
| $E_{AS}^{*}$         | Single Pulsed Avalanche Energy                   | $V_{DD}=50\text{ V}, L=0.5\text{ mH}$         | -   | 392      | mJ                   |
| $T_J, T_{stg}$       | Operating Junction and Storage Temperature Range |                                               | -55 | 150      | $^{\circ}\text{C}$   |
| $R_{\theta JA}^{**}$ | Thermal Resistance-Junction to Ambient           |                                               | -   | 56       | $^{\circ}\text{C/W}$ |
| $R_{\theta JC}$      | Thermal Resistance-Junction to Case              |                                               | -   | 1.85     |                      |

Notes:

- \* Pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- \*\* Surface mounted on 1 in<sup>2</sup> pad area,  $t \leq 10\text{ sec}$ .
- \*\*\* Limited by bonding wire.

## 4. Marking Information

| Product Name | Marking            |
|--------------|--------------------|
| KJ09N10C     | KJ09N10C<br>XXXXXX |

## 5. Ordering Code

| Product Name | Package | Reel Size | Tape width | Quantity(pcs) |
|--------------|---------|-----------|------------|---------------|
| KJ09N10C     | TO-220  | N/A       | N/A        | 1000          |

Note: KUAIJIE XIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

## 6. Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| Symbol                                   | Parameter                        | Conditions                                                                                   | Min | Typ  | Max  | Unit |
|------------------------------------------|----------------------------------|----------------------------------------------------------------------------------------------|-----|------|------|------|
| Static Characteristics                   |                                  |                                                                                              |     |      |      |      |
| BV <sub>DSS</sub>                        | Drain-Source Breakdown Voltage   | V <sub>GS</sub> =0 V, I <sub>DS</sub> =250 μA                                                | 100 | -    | -    | V    |
| V <sub>GS(th)</sub>                      | Gate Threshold Voltage           | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250 μA                                   | 1.2 | 1.8  | 2.6  | V    |
| I <sub>DSS</sub>                         | Zero Gate Voltage Source Current | V <sub>DS</sub> =80 V, V <sub>GS</sub> =0 V                                                  | -   | -    | 1    | μA   |
| I <sub>GSS</sub>                         | Gate Leakage Current             | V <sub>DS</sub> =0 V, V <sub>GS</sub> =±20 V                                                 | -   | -    | ±100 | nA   |
| R <sub>DS(ON)</sub> <sup>a</sup>         | On-State Resistance              | V <sub>GS</sub> =10 V, I <sub>DS</sub> =20 A                                                 | -   | 8.5  | 9.5  | mΩ   |
|                                          |                                  | V <sub>GS</sub> =4.5 V, I <sub>DS</sub> =10 A                                                | -   | 10.5 | 13.5 |      |
| g <sub>FS</sub> <sup>b</sup>             | Forward Transconductance         | V <sub>GS</sub> =5 V, I <sub>DS</sub> =10 A                                                  | -   | 30   | -    | S    |
| R <sub>g</sub>                           | Gate Resistance                  | f=1 MHz                                                                                      | -   | 0.6  | -    | Ω    |
| Diode Characteristics                    |                                  |                                                                                              |     |      |      |      |
| V <sub>SD</sub> <sup>a</sup>             | Diode Forward Voltage            | I <sub>SD</sub> =20 A, V <sub>GS</sub> =0 V                                                  | -   | 0.9  | 1.3  | V    |
| t <sub>rr</sub>                          | Reverse Recovery Time            | I <sub>DS</sub> =20 A, V <sub>GS</sub> =0V<br>dI <sub>SD</sub> /dt=100 A/μs                  | -   | 43   | -    | ns   |
| Q <sub>rr</sub>                          | Reverse Recovery Charge          |                                                                                              | -   | 36   | -    | nC   |
| Dynamic Characteristics <sup>b</sup>     |                                  |                                                                                              |     |      |      |      |
| C <sub>iss</sub>                         | Input Capacitance                | V <sub>GS</sub> =0 V, V <sub>DS</sub> =50 V<br>Frequency=1 MHz                               | -   | 1644 | -    | pF   |
| C <sub>oss</sub>                         | Output Capacitance               |                                                                                              | -   | 359  | -    |      |
| C <sub>rss</sub>                         | Reverse Transfer Capacitance     |                                                                                              | -   | 13.5 | -    |      |
| t <sub>d(on)</sub>                       | Turn-on Delay Time               | V <sub>DS</sub> =50 V, V <sub>GEN</sub> =10 V,<br>R <sub>G</sub> =3 Ω, I <sub>DS</sub> =20 A | -   | 17   | -    | ns   |
| t <sub>r</sub>                           | Turn-on Rise Time                |                                                                                              | -   | 1    | -    |      |
| t <sub>d(off)</sub>                      | Turn-off Delay Time              |                                                                                              | -   | 43   | -    |      |
| t <sub>f</sub>                           | Turn-off Fall Time               |                                                                                              | -   | 8.2  | -    |      |
| Gate Charge Characteristics <sup>b</sup> |                                  |                                                                                              |     |      |      |      |
| Q <sub>g</sub>                           | Total Gate Charge                | V <sub>DS</sub> =50 V, V <sub>GS</sub> =10 V,<br>I <sub>DS</sub> =20 A                       | -   | 29   | -    | nC   |
| Q <sub>gs</sub>                          | Gate-Source Charge               |                                                                                              | -   | 5.6  | -    |      |
| Q <sub>gd</sub>                          | Gate-Drain Charge                |                                                                                              | -   | 6.5  | -    |      |

Notes:

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

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## 7. Typical Characteristics

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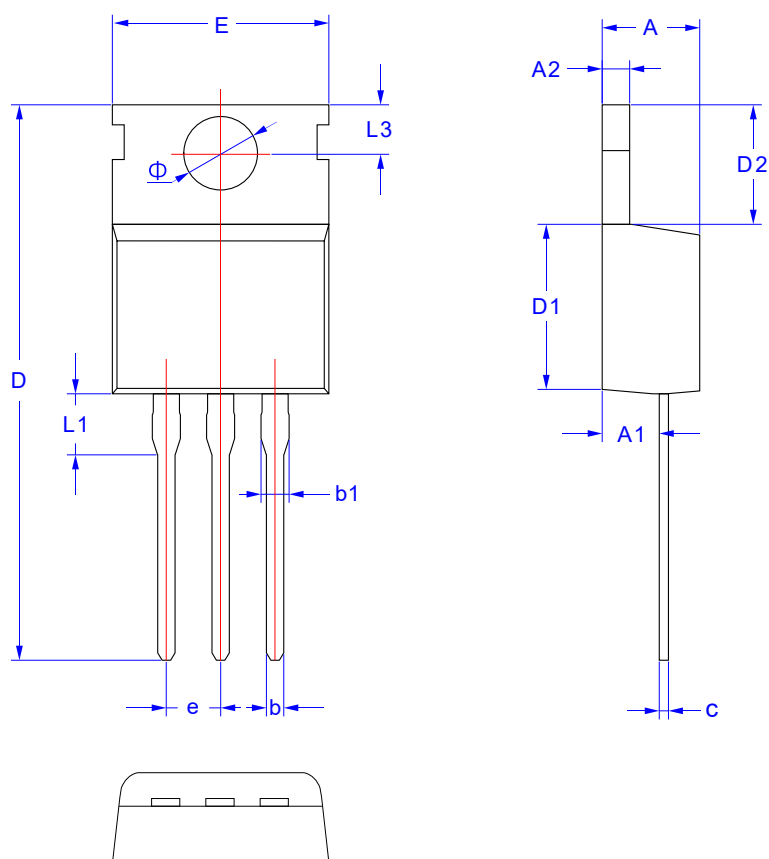
## 7. Typical Characteristics (cont.)

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## 8. Package Dimensions

### TO-220 Package



| Symbol | Dimensions in Millimeters |       |
|--------|---------------------------|-------|
|        | MIN                       | MAX   |
| A      | 4.24                      | 4.70  |
| A1     | 2.20                      | 3.00  |
| b      | 0.70                      | 0.95  |
| b1     | 1.14                      | 1.70  |
| c      | 0.40                      | 0.60  |
| c1     | 1.15                      | 1.40  |
| D      | 28.0                      | 29.8  |
| D1     | 8.80                      | 9.90  |
| E      | 9.70                      | 10.50 |
| L1     | 3.80                      |       |
| L2     | 6.25                      | 6.90  |
| L3     | 2.40                      | 3.00  |
| e      | 2.54 BSC                  |       |